

THYRISTOR MODULE PWA150SA



FEATURES

- ☞ **IT(AV) 90A (each device)**
- ☞ **High surge current 1800A (60Hz)**
- ☞ **Easy Construction**
- ☞ **Non-insulated Mounting base as common**
- ☞ **Anode Terminal**

TYPICAL APPLICATIONS

- ☞ **Welders**
- ☞ **Various DC power supply**

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MODULE
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TECHNICAL DATA

DEVICE TYPE

**V_{RRM}
(V)**

**V_{RSM}
(V)**

PWA150SA-3	300	400
PWA150SA-4	400	500
PWA150SA-6	600	700

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITION	RATINGS	UNIT
I_T (RMS)	RMS on-state current		230	A
I_T (AV)	Average on-state current	Three-phase, half-wave, $T_c=119^\circ\text{C}$	150	A
I_{TSM}	Surge (non-repetitive) on-state current	One half cycle at 60Hz, peak value	3000	A
I_t^2	I_t^2 for fusing	Value for one cycle of surge current	3.8×10^5	A^2s
di/dt	Critical rate of rise of on-state current	$V_D=1/2V_{DRM}$, $I_G=1.0\text{A}$, $T_j=150^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
PGM	Peak gate power dissipation		5.0	W
PG (AV)	Average gate power dissipation		0.5	W
VFGM	Peak gate forward voltage		10	V
VRGM	Peak gate reverse voltage		5.0	V
IFGM	Peak gate forward current		2.0	A
T_j	Junction temperature		$-40 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-40 \sim +125$	$^\circ\text{C}$
—	Mounting torque	Main terminal screw M8	8.83~10.8	N·m
			90~110	kg·cm
		Mounting screw M6	1.96~2.94	N·m
			20~30	kg·cm
—	Weight	Typical value	250	g

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ELECTRICAL CHARACTERISTICS OF IGBT

SYMBOL	PARAMETER	TEST CONDITION	LIMITS			UNIT
			MIN	TYP	MAX	
IRRM	Repetitive peak reverse current	T _J =150°C, V _{RRM} applied	—	—	40	mA
IDRM	Repetitive peak off-state current	T _J =150°C, V _{DRM} applied	—	—	40	mA
V _{TM}	On-state voltage	T _J =150°C, I _{TM} =450A, instantaneous meas.	—	—	1.2	V
dv/dt	Critical rate of rise of off-state voltage	T _J =150°C, V _D =2/3V _{DRM}	200	—	—	V/μs
V _{GT}	Gate trigger voltage	T _J =25°C, V _D =6V, R _L =2Ω	—	—	3.0	V
V _{GD}	Gate non-trigger voltage	T _J =150°C, V _D =1/2V _{DRM}	0.25	—	—	V
I _{GT}	Gate trigger current	T _J =25°C, V _D =6V, R _L =2Ω	15	—	100	mA
R _{th (j-c)}	Thermal resistance	Junction to case (per 1/3 module)	—	—	0.15	°C/W
R _{th (c-f)}	Contact thermal resistance	Case to fin, conductive grease applied (per 1/3 module)	—	—	0.15	°C/W

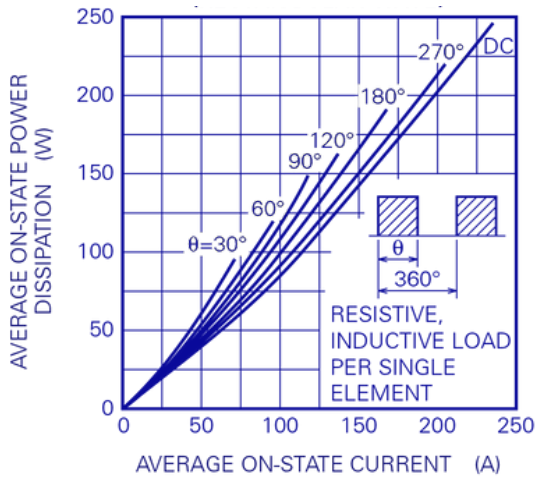
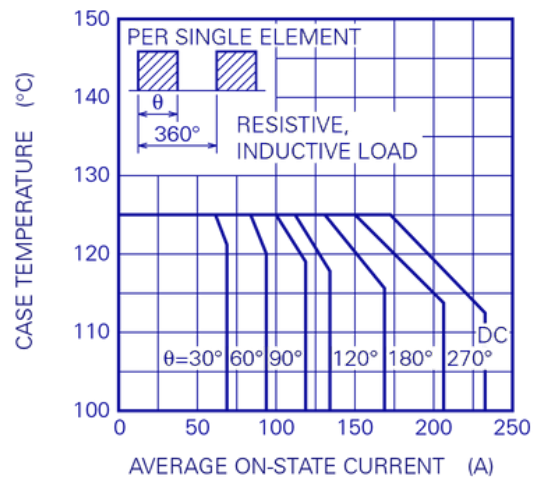


FIG. 2 limiting value of the average on-state current (rectangular wave)

FIG. 1 maximum average on-state power dissipation (rectangular wave)



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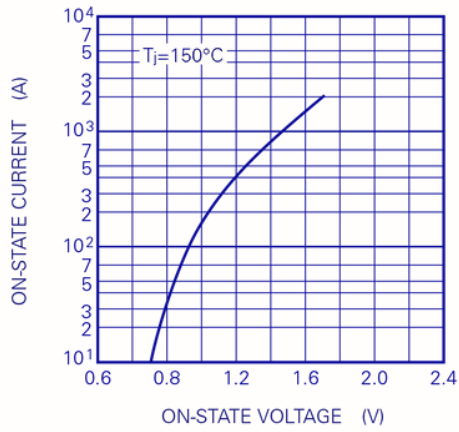


FIG. 3 maximum on-state characteristic

FIG. 4 gate characteristics

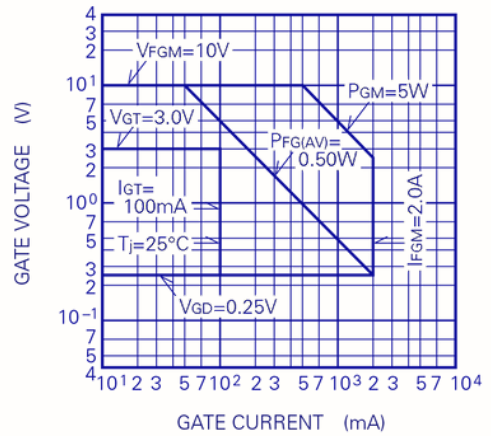
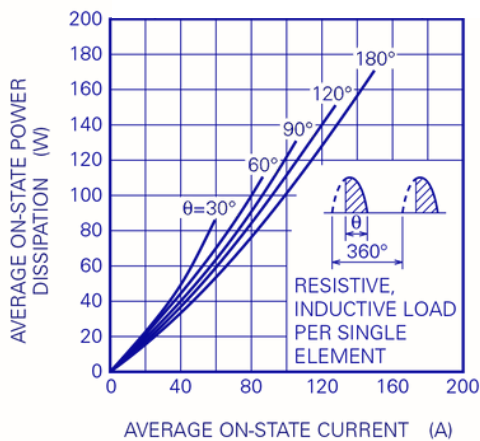


FIG. 5 maximum average on-state power dissipation (single phase halfwave)



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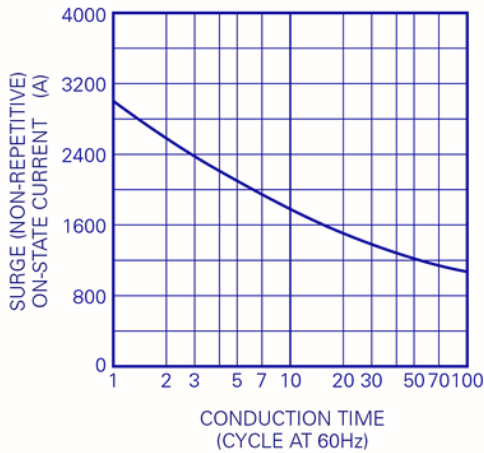


FIG. 6 rated surge (non-repetitive) on-state current

FIG. 7 maximum transient thermal impedance (junction to case)

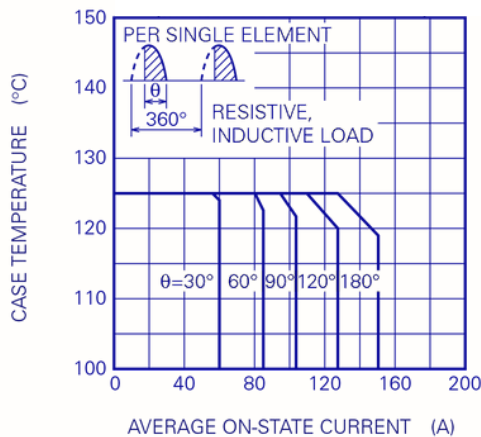
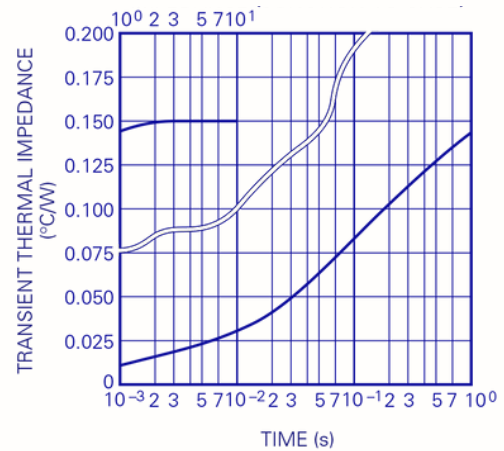


FIG. 8 limiting value of the average on-state current (single phase halfwave)

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PACKAGE OUTLINE

